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**Uji, Japan
1-2 June 2017**



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IWJT2017, Kyoto, Japan, June 1-2, 2017

June 1 (Thursday)

9:00 Registration

9:45 Opening Remarks

Keynote Speech

10:00 KN-1 **Nano-devices with advanced junction engineering and improved energy efficiency** 1
Adrian Mihai Ionescu (EPFL)

10:40 Break (10min)

Session 1 Doping Technologies (1)

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[Invited] Michael I. Current (Current Scientific)

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Tetsuya Igo (Nissin Ion Equipment)

11:40 S1-3 **Nanometer-deep Junctions with High Doping Concentration for Ge SDEs using Solid Source Doping and Flash Lamp Annealing** 15
Hideaki Tanimura (SCREEN Semiconductor Solutions)

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